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T-41-61

DEVICE NO. AT023PT
SILICON PHOTOTRANSISTOR CHIPS

I、Scope:

The specification applies to NPN silicon Phototransisitor chips,
Device No. AT023PT

II、Structure:

2-1. Planar Type

2-2. Electrodes

N (Collector) side: Gold Alloy

P (Base) side: Aluminum

N (Emitter) side: Aluminum

III、Size:

3-1. Chip size: 24 mils × 24 mils (0.6mm × 0.6mm)

3-2. Chip thickness: 7 +/ -1.5 mils (0.178 +/ -0.038mm)

3-3. Active Area: 17 mils × 17mils (0.432mm × 0.432 mm)

3-4. Pattern Drawing: Refer to the attached Drawing

IV、Electro-optical Characteristics (T_a=25℃)

PARAMETER	SYMBOL	CONDITION	MIN	TYP	MAX	UNIT
Collector Emitter Breakdown Voltage	BV_{CEO}	I_C=100 μA I_B=0	30	--	--	V
Emitter-Collector Breakdown Voltage	BV_{ECO}	I_E=100 μA I_B=0	5	--	--	V
Collector Dark Current	I_{CEO}	V_{CE}=10V H =0mw/cm^2	--	--	100	nA
Collector-Emitter Saturation Voltage	$V_{CE(S)}$	V_{CEO}=0.1 mA H=2.5mw/cm^2	--	--	0.8	V
Rise\Fall Time	Tr/Tf	V_{CE}=5V I_C=1mA,R_L=100ohm	--	3/3	--	μS
Photo Current	I_L	V_{CE}=5V H=2.5mw/cm^2 (GaAs I_{RED})	300	--	--	μA

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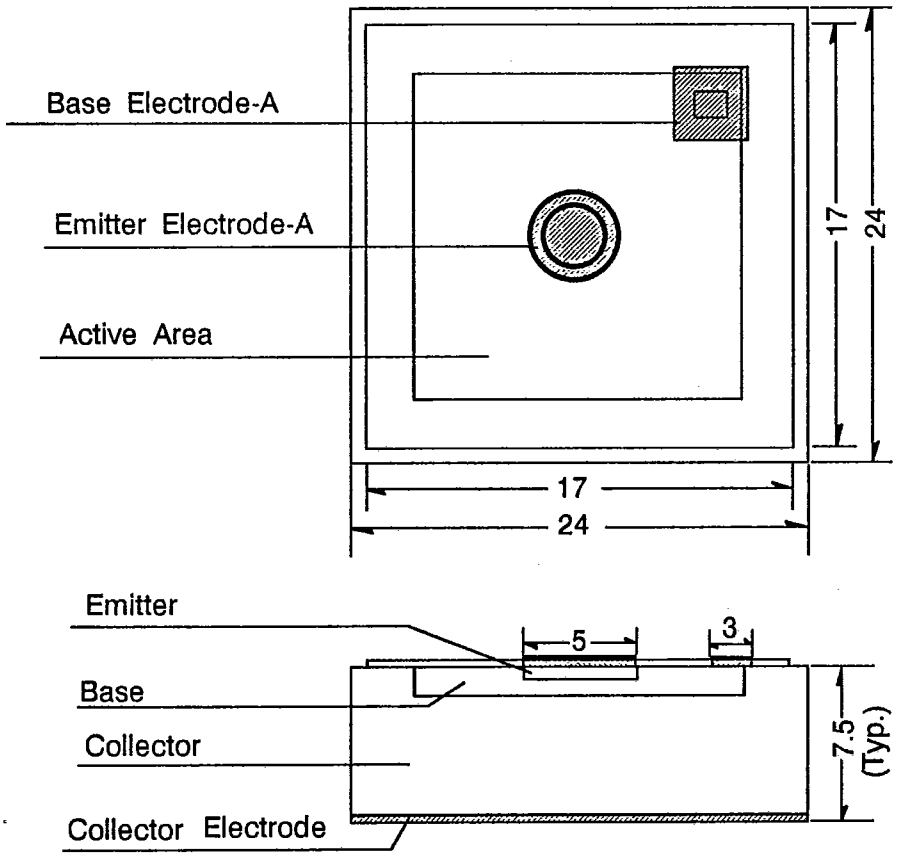
Fig. : ATO23PT Pattern Drawing

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